MAGONE, J.

In the Presidium of the Academy of Sciences of the Latvian S.S.R.
Vestis Latv ak no.8:152 '61.

MAGONE, Ya.[Magone, J.]

Conference of leading scientific workers of the Academy of Sciences of the Latvian S.S.R. Vestis Latv ak no.7:141-143 '61.

(Academy of Sciences of the Latvian S.S.R.)
(Latvia--Scientists--Congresses)

APPROVED FOR RELEASE: 06/23/11: CIA-RDP86-00513R001031400039-6

MAGONE, J.

In the Presidium of the Latvian Academy of Sciences. Vestis Latv ak no.6:183-184 '61.

(Academy of Sciences of the Latvian S.S.R.)

MAGONE, J.

Contribution of science to the national economy. Vestis Latv ak no.6:173 '61.

(Agriculture)

MAGONE, J.

At the Presidium of the Academy of Sciences of the Latvian SSR.
Vestis Latv ak no.4:183 '61. (EEAI 10:9)

(Academy of Sciences of the Latvian S.S.R.)

MAGONE, J.

Activity of scientists in connection with the construction of the Plavinas Hydroelectric-Power Station. Vestis Latv ak no.4:170 '61. (EEAI 10:9)

(Hydroelectric-power stations) (Scientists)

MAGONE, Ya. [Magone, J.]

General meeting of the Academy of Sciences of the Latvian SSR in 1961. Vestis Latv ak no.4:153-156 '61. (EEAI 10:9)

(Academy of Sciences of the Latvian S.S.R.)

MAGONE, J.

In the Presidium of the Academy of Sciences of the Latvian S.S.R.
Vestis Latv ak no.3:168 '61.

MAGONE, J.

Scientific conference on questions of winter hardiness of cultivated plants. Vestis Latv ak no.2:182 '61. (EEAI 10:9)

(Plants)

MAGONE, J.

Scientific conference on the vibromixing method. Vestis Latv ak no.2:181-182 '61. (EEAI 10:9)

(Vibrated concrete)

MAGONE, J.

Sessions and conferences of the Academy of Sciences of the Latvian S.S.R. in 1960. Vestis Latv ak no.2:179-181 '61.

MAGONE, J.

In the Presidium of the Academy of Sciences of the Latvian S.S.R.
Vestis Lety ak no.1:182-184 '61.

MAGONE, J.

At the Presidium of the Latvian Academy of Sciences. Vestis Latv ak no.12:186 '60. (EEAI 10:9)

(Academy of Sciences of the Latvian S.S.R.)

MAGONE, Ya.[Magone, J.]

Concerning the work of the All-Union Coordination Commission on Microelements. Vestis Latv ak no.12:163-164 '60.
(EEAI 10:9)

(Trace elements)

MAGONE, J.

At the Presidium of the Latvian Academy of Sciences. Vestis Latv ak no.10:191 '60. (EEAI 16:9:10)

(Academy of Sciences of the Latvian S.S.R.)

MAGONE, J.

At the Presidium of the Latvian Academy of Sciences. Vestis Latv ak no.9:191 '60. (EEAI 10:9)

(Academy of Sciences of the Latvian S.S.R.)

MAGONE, J.

Grand meeting of the Academy of Sciences dedicated to the 20th anniversary of Soviet Latvia. Vestis Latv ak no.7:229-230 '60. (EEAI 10:7)

(Latvia--History) (Academy of Sciences of the Latvian SSR)

MAGONE, I.

Interrepublic conference of physicians. Vestis Latv ak no.6:207 '60. (EEAI 10:9)

(RUSSIA--MEDICINE)

MAGONE, J.

At the Presidium of the Academy of Sciences of the Latvian SSR.
Vestis Latv ak no.4:207 '60. (EEAI 10:7)
(Academy of Sciences of the Latvian SSR)

MAGONE, J.

The Second Inter-Republic Coordination Conference on Parasitological Problems. Vestis Latv ak no.4:202 '60. (EEAI 10:7)
(Baltic States—Parasitology) (White Russia—Parasitology)

MAGONE, Ya.[Magone,J.]

Microelements; the enlarged Conference of the All-Union Coordination Commission on Microelements. In Russian. Vestis Latv ak no.3:189-192 '60. (EEAI 10:7)
(Trace elements)

MAGONE, J.

At the Presidium of the Academy of Sciences of the Latvian SSR.
Vestis Latv ak no.3:188 '60. (EEAI 10:7)
(Academy of Sciences of the Latvian SSR)

MAGONE, YA. [Magone, J.]

General meeting of the Academy of Sciences of the Latvian SSR on February 11, 1960. In Russian. Vestis Latv ak no.3:21-25 '60. (EEAI 10:7)

(Academy of Sciences of the Latvian SSR)

APPROVED FOR RELEASE: 06/23/11: CIA-RDP86-00513R001031400039-6

MAGONE, J.

At the Presidium of the Latvian Academy of Sciences. Vestis Latv ak no.2:207 '60. (EEAI 10:1)
(Academy of Sciences of the Latvian SSR)

MAGONE, J.

Scientific sessions and conferences of the Latvian Academy of Sciences in 1959. Vestis Latv ak no.2:203-206 '60. (EEAI 10:1)
(Academy of Sciences of the Latvian SSR)

MAGONE, Yu. [Magone, J.]

In commemoration of the late P.I.Stradins and the unveiling of his tombstone. Vestis Latv ak no.2:196 '60. (EEAI 10:1)
(Stradins, Pauls) (Physicians, Latvian)

MAGONE, Ya. [Magone, J.]

Conference on problems of nourishment of healthy and sick persons. Vestis Latv ak no.1:202-206 '60. (EEAI 9:11)
(Food)

MAGONE, Ya. [Magone, J.]

Grand meeting dedicated to the 150th anniversary of the birth of Charles Darwin. Vestis Latv ak no.12:175-176 '59. (EEAI 9:11)
(Darwin, Charles Robert)
(Evolution)

MAGONE, J.

At the Presidium of the Latvian Academy of Sciences. Vestis Latv ak no.12:174 '59. (EEAI 9:11)
(Academy of Sciences of the Latvian S.S.R.)

MAGONE, J.

At the Presidium of the Latvian Academy of Sciences. p. 175.

LATVIJAS PSR ZINATNU AKADEMIJA. VESTIS. RIGA, LATVIA. No. 7, 1959

Monthly List of East European Accessions. (EEAI) LC, Vol. 9, no. 2, Feb. 1960 Uncl.

MAGONE, J.

GENERAL

PERIODICALS: VECTIS, NO. 6, 1958

MAGONE, J. Scientific Conference of the Section of Social Sciences of the Latvian Academy ofSciences. p. 159.

Monthly list of East European Accessions (EEAI) LC, VOL. 8, No. 2
February 1959, Unclass.

[redacted], J.

GENERAL

PERIODICALS: VESTIS No. 1, 1958

[redacted], J. Scientific conferences and sessions of the Latvian Academy of Sciences in 1957. p. 162.

Monthly list of East European Accessions (EPM-) LC, Vol. 8, No. 2, February 1959, Unclass.

MAGONE, Y.

Decisions of the Presidium of the Academy of Sciences of the Latvian S.S.R.
Latv. PSR Zin.Akad.Vēstis no.2:139 '52. (MLRA 6:6)
(Academy of Sciences of the Latvian S.S.R.)

1. MAGONE, J.

2. USSR 600

4. Reclamation of Land - Ogre

7. Session of the scientific council of the Land Reclamation Institute in Ogre, Latv. PSR Zin Akad Vestis, No. 12, 1951.

9. Monthly List of Russian Accessions, Library of Congress, April 1953, Uncl.

1. J. MAGONE

2. USSR (600)

4. Agriculture

7. Joint scientific session on problems of biology and agriculture. Latv. PSR Zin. Akad. Vestis no. 11. 1951

9. Monthly List of Russian Accessions, Library of Congress, April 1953, Uncl.

1. MAGONE, J.

2. USSR (600)

4. Language and Languages

7. Scientific session of the Academy of Sciences dedicated to the first anniversary of publication of Comrade I. V. Stalin's outstanding work "Marxism and problems of linguistics." Latv.PSR Zin Akad Vestis No. 6 1951.

9. Monthly List of Russian Accessions, Library of Congress, April 1953, Uncl.

MAGONE, J.

Sessions and conferences of the Latvian Academy of Sciences of the S.S.R. in 1963. Izv.AN Latv.SSR no.2:120-121 '64.

Presidium of the Academy of Sciences of the Latvian S.S.R.
Ibid.:112 (MIRA 17:4)

MAGONE, J.

In the Presidium of the Academy of Sciences of the Latvian S.S.R. Izv. AN Latv. SSR no.5:153 '63. (MIRA 17:1)

1. [illegible], J.

2. USSR (600)

4. Latvia - Reclamation of Land

7. Out-of-town session of the Land [illegible] Institute of the Academy of Sciences of the Latvian S.S.R. in Jelgava.
Latv. PSR Zin. Zemk, Vestis 2, 1951

9. Monthly List of Russian Accessions, Library of Congress, January 1953, Unclassified.

1. MAGONE, J.

2. USSR (600)

4. Latvia - Reclamation of Land

7. Out-of-town session of the Land Reclamation Institute of the Academy of Sciences of the Latvian S.S.R. in Jelgava.
Latv. PSR Zin Akad. Vestis 1, 1951

9. Monthly List of Russian Accessions, Library of Congress, January 1953. Unclassified.

1. MAGONE, J.

2. USSR (600)

4. Reclamation of Land - Latvia

7. Out-of-town session of the Land Reclamation Institute of Academy of Sciences of the Latvian S.S.R. in Valmiera. Latv.PSR Zin.Akad. Vestis no. 10, 1950.

9. Monthly Lists of Russian Accessions, Library of Congress, March 1953, Unclassified.

MAGONE, YA.

29115 Vyezdnaya sessiya Akademii nauk Latviyskoy SSR v g. Daugavpilse (po voprosam razvitiya kolkhoznogo stroitel'stva v Respublike, iyun' 1949 g.) Izvestiya Akad. Nauk Latv. SSR, 1949, No.8, s. 143-52 -- Na Latysh. i rus. yaz.

SO: Letopis' Zhurnal'nykh Statey, Vol. 39, Moskva, 1949

MAGONE, J.

In the Presidium of the Academy of Sciences of the Latvian S.S.R.
Izv. AN Latv. SSR no.5:154 '62. (MIRA 16:7)
(Academy of Sciences of the Latvian S.S.R.)

MAGONE, J.

In the Presidium of the Academy of Sciences of the Latvian S.S.R.
Izv. AN Latv.SSR no.3:136 '63.

(MIRA 16:5)

(Academy of Sciences of the Latvian S.S.R.)

MAGONE, J.

Sessions and conferences of the Academy of Sciences of the Latvian S.S.R. in 1962. Izv.AN Latv.SSR no.2:136-138 '63.
(MIRA 16:4)
(Academy of Sciences of the Latvian S.S.R.)

BELEKHOV, Gennadiy Petrovich; CHUBINSKAYA, Alla Aleksandrovna; MAGON, E.E., red.

[Mineral and vitamin nutrition of farm animals] Mineral'noe i vitaminnoe pitanie sel'skokhoziaistvennykh zhivotnykh. Izd.2., perer. i dop. Leningrad, Kolos, 1965. 297 p. (MIRA 19:1)

VOROB'YEV, Viktor Vasil'yevich; STEPANCHUK, Anatoliy Andreyevich; MAGON, E.E., red.

[Raising calves and piglets with the use of milk substitutes] Vyrashchivanie telyat i porosiat s ispol'zovaniem zamenitelei moloka. Leningrad, Kolos, 1965. 54 p. (MIRA 19:1)

DMITROCHENKO, A.P., prof., red.; MAGON, E.E., red.

[Feeding and raising young farm animals; collection of scientific work] Kormlenie i vyrashchivanie molodniaka sel'skokhoziaistvennykh zhivotnykh; sbornik nauchnykh rabot. Moskva, Izd-vo "Kolos." No.5. 1964. 315 p. (MIRA 17:4)

1. Leningradskiy sel'skokhozyaystvennyy institut (for Dmitrochenko).

LEBEDEV, M.M., prof., red.; MAGON, E.E., red.

[Heredity and variability in farm animals; collection of scientific papers] Nasledstvennost' i izmenchivost' sel'skokhoziaistvennykh zhivotnykh; sbornik nauchnykh trudov, Pod red. M.M.Lebedeva. Leningrad, Izd-vo "Kolos," 1964. 214 p. (MIRA 17:6)

1. Pushkino. Nauchno-issledovatel'skaya laboratoriya po razvedeniyu sel'skokhozyaystvennykh zhivotnykh.

DRURI, Ivan Vasil'yevich, kand. sel'khoz. nauk; MITYUSHEV, Pavel Vasil'yevich, kand. biol. nauk; MAGON, E.E., red.; BARANOVA, L.G., tekhn. red.

[Deer raising] Olenevodstvo. Moskva, Sel'khozizdat, 1963. 242 p. (MIRA 16:8)
(Deer) (Antlers)

MAKAROVA, Mariya Mikhaylovna; MAGON, E.E., red.; BARANOVA, L.G., tekhn. red.

[Microbiology of silage] Mikrobiologiia silosa. Leningrad, Sel'khozizdat, 1962. 190 p. (MIRA 16:4)
(Ensilage--Microbiology)

KAARMA, Iokhannes Yanovich; OSIN, Nikolay Petrovich; LAANMYAE, Vambola Eduardovich [Laanmäe, V.]; MAGON, E.E., red.; BARANOVA, L.G., tekhn. red.

[Estonian meat-type swine] Estonskaia bekonnaia poroda svinei. Leningrad, Sel'khozizdat, 1962. 109 p. (MIRA 16:4)
(Estonia--Swine breeding)

SHCHERBOV, Nikita Antonovich, prof.; MAGON, E.E., red.; BARANOVA, L.G., tekhn. red.

[Keeping suckling sows with baby pigs in groups]Gruppovoe soderzhanie podsosnykh matok s porosiatami. Leningrad, Sel'khozizdat, 1962. 78 p. (MIRA 15:11)

(Swine)

DMITROCHENKO, Aleksandr Petrovich, zasl. deyatel' nauki RSFSR; PSHENICHNYY, Pavel Dmitriyevich, akademik; MAGON, E.E., red.; BARANOVA, L.G., tekhn. red.

[Feeding farm animals] Kormlenie sel'skokhoziaistvennykh zhivotnykh. Leningrad, Izd-vo sel'khoz. lit-ry, zhurnalov i plakatov, 1961. 527 p. (MIRA 15:1)

1. Ukrainskaya akademiya sel'skokhozyaystvennykh nauk (for Pshenichnyy).

(Feeding)

MAGOMETOV, A.Z.

Case of uncorrected left inguinoscrotal hernia in an eight-year-old child. Khirurgiia 35 no.3:102 Mr '59.
(MIRA 12:8)

1. Iz Kurchaloyevskoy rayonnoy bol'nitsy (glavnyy vrach O.G.Solomanyuk) Checheno-Ingushskoy ASSR.
(HERNIA)

1. MAGOMETOV, A. A.

2. USSR (600)

4. Kubachi Dialect - Phonetics

7. Sound m in the Kubachi dialect of the Darghin language. Soob. AN Gruz. SSR 11, No. 7, 1950.

9. Monthly List of Russian Accessions, Library of Congress, May 1953, Uncl.

MAGOMEDOVA, A. I.

MAGOMEDOVA, A. I.: "The use of chloromycetin and sintomycin to treat progressive and other purulent ulcers of the corneal membrane." Min Health USSR. Central Inst of the Advanced Training of Physicians. Moscow, 1956.
(Dissertation for the Degree of Candidate in Medical Science)

So: Knizhanava Letopis, No 17, 1956

L 21225-66
ACC NR: AP6003821

different mechanisms (electronic and phonon) of thermal conductivity in semiconductors. A jump in the thermal conductivity by a factor of two is observed during melting, and a jump in the electric conductivity by a factor of 5.4. Further heating in the liquid state is accompanied by an increase in the electric conductivity and thermal conductivity. The latter reaches a maximum at 985K. The electric conductivity continues to rise with increasing temperature and is connected with the metallization of the bonds between the elements of the compound. It is concluded that gallium antimonide is a semiconductor in the solid state and in the melting region, and has metallic properties in the liquid state. The variation of the short-range order during melting influences all the components of the thermal conductivity. Orig. art. has: 2 figures and 1 formula.

SUB CODE: 20/ SUBM DATE: 20Feb65/ ORIG REF: 019/ OTH REF: 002

Card 2/2 dda

L 21225-66 EWT(m)/EWP(t) IJP(c) JD

ACC NR: AP6003821 SOURCE CODE: UR/0181/66/008/001/0290/0292

AUTHOR: Amirkhanov, Kh. I.; Magomedov, Ya. B.

ORG: Institute of Physics, Dagestan Branch AN SSSR, Makhachkala (Institut fiziki Dagestanskogo filiala AN SSSR)

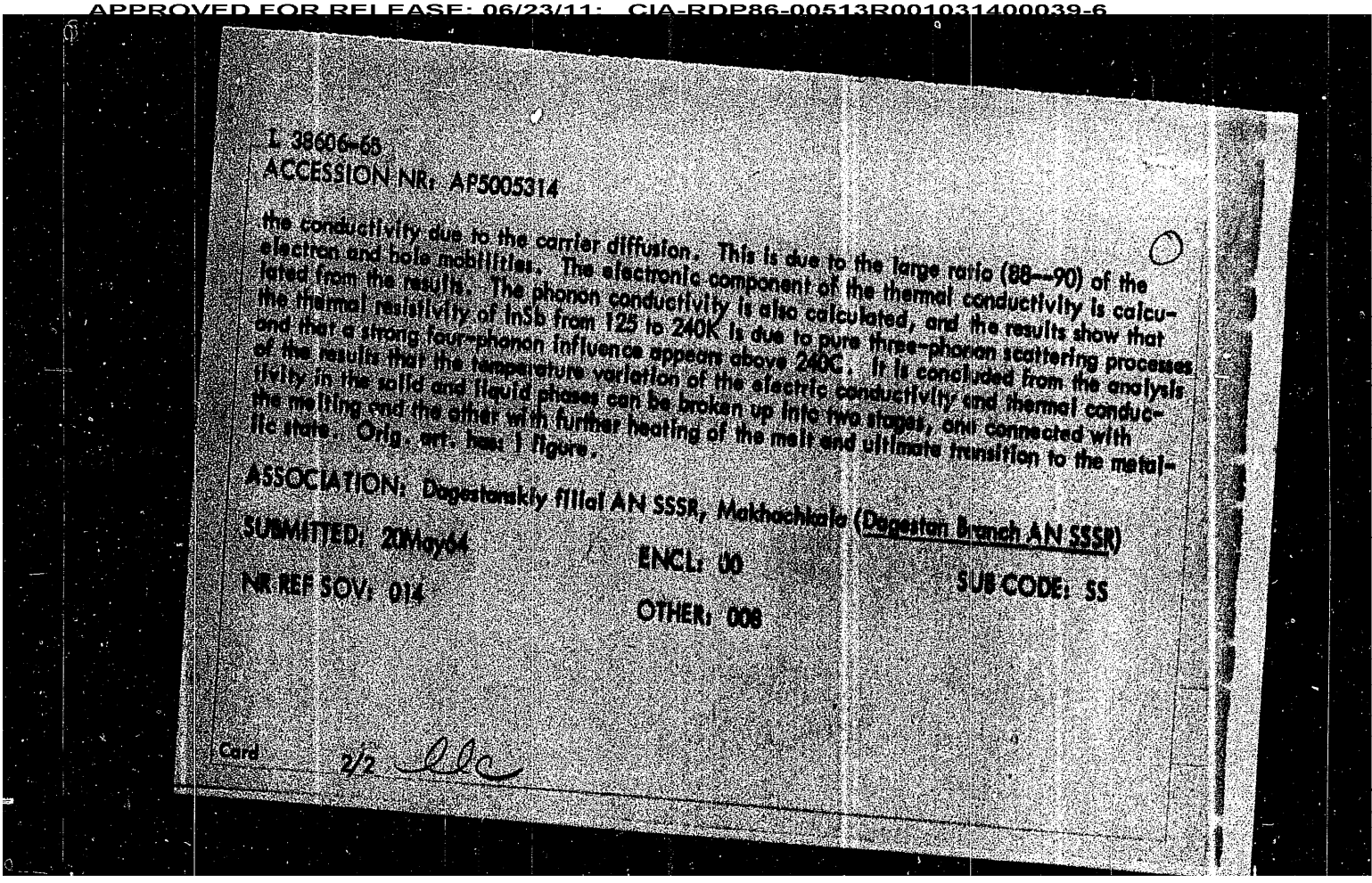
TITLE: Thermal conductivity of gallium antimonide in solid and liquid states

SOURCE: Fizika tverdogo tela, v. 8, no. 1, 1966, 290-292

TOPIC TAGS: gallium alloy, thermal conduction, ordered alloy, semiconductor alloy, electric conductivity, heat change of state, melting, temperature dependence

ABSTRACT: The purpose of the investigation was to clarify the mechanism of the thermal conductivity and the effect of short-range order on its component parts. The thermal conductivity was measured by an absolute method under stationary thermal conditions, as described elsewhere (Izv. AN AzSSR v. 4, 3, 1946) in an argon atmosphere, using polycrystalline samples of p-type GaSb with carrier density 3.6×10^{10} cm^{-3}. The data obtained at room temperature agree well with the published results. This is claimed to be the first information on the temperature dependence of the thermal conductivity of GaSb at high temperatures and in the liquid states. The results are interpreted from the point of view that there are several

Card 1/2



L 38606-65
ACCESSION NR: AP5005314

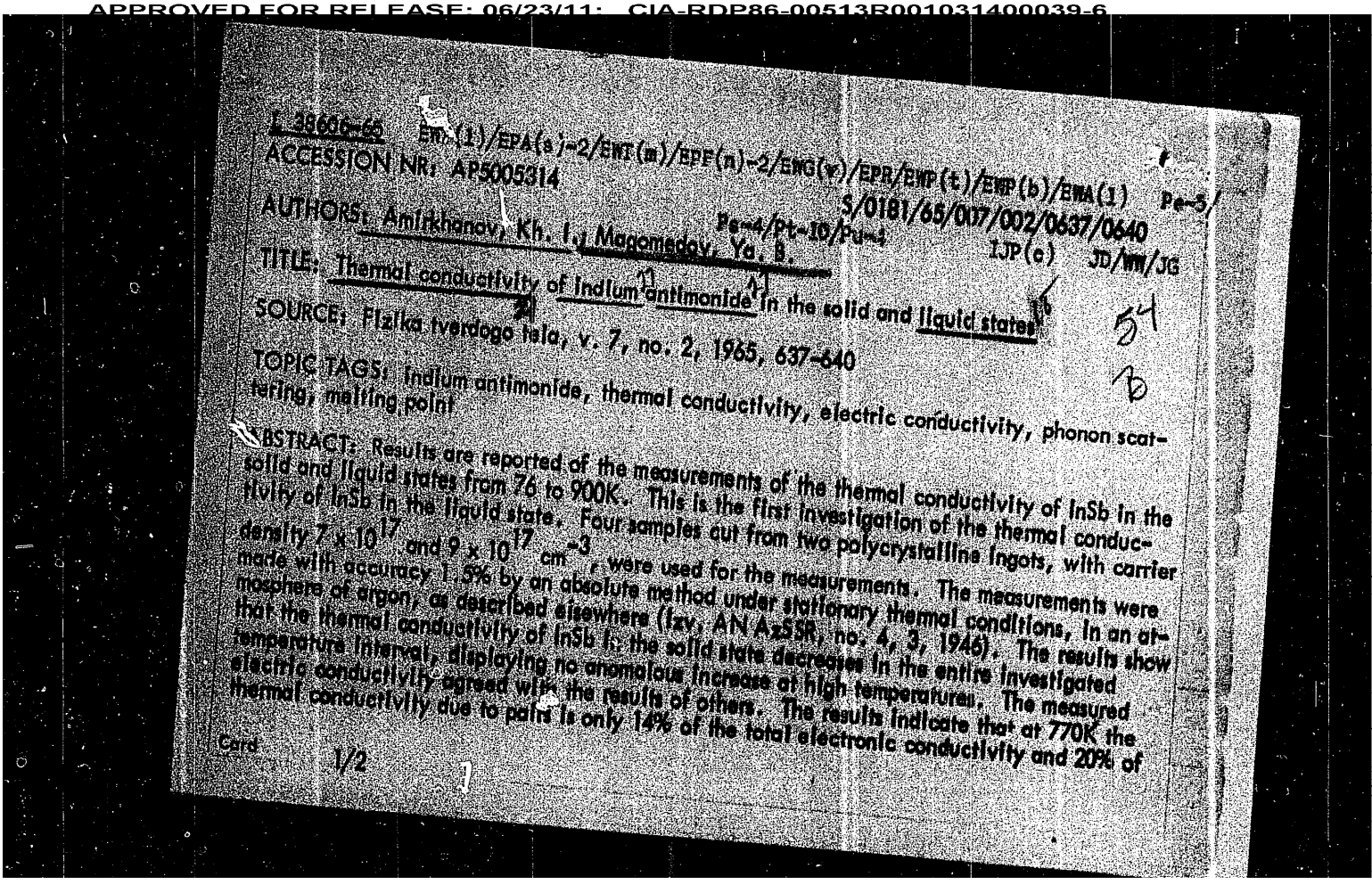
the conductivity due to the carrier diffusion. This is due to the large ratio (88--90) of the electron and hole mobilities. The electronic component of the thermal conductivity is calculated from the results. The phonon conductivity is also calculated, and the results show that the thermal resistivity of InSb from 125 to 240K is due to pure three-phonon scattering processes and that a strong four-phonon influence appears above 240C. It is concluded from the analysis of the results that the temperature variation of the electric conductivity and thermal conductivity in the solid and liquid phases can be broken up into two stages, one connected with the melting and the other with further heating of the melt and ultimate transition to the metallic state. Orig. art. has: 1 figure.

ASSOCIATION: Dagestanskiy filial AN SSSR, Makhachkala (Dagestan Branch AN SSSR)

SUBMITTED: 20May64 ENCL: 00 SUB CODE: SS

NR REF SOV: 014 OTHER: 008

Card 2/2



L 38606-66 EWT(1)/EPA(s)-2/EWT(m)/EPF(n)-2/EWG(v)/EPR/EWP(t)/EWP(b)/EWA(1) Pe-5/
ACCESSION NR: AP5005314 S/0181/65/007/002/0637/0640
Pe-4/Pt-10/Pu-4 IJP(c) JD/WW/JG

AUTHORS: Amirkhanov, Kh. I.; Magomedov, Ya. B.

TITLE: Thermal conductivity of indium antimonide in the solid and liquid states

SOURCE: Fizika tverdogo tela, v. 7, no. 2, 1965, 637-640

TOPIC TAGS: indium antimonide, thermal conductivity, electric conductivity, phonon scattering, melting point

ABSTRACT: Results are reported of the measurements of the thermal conductivity of InSb in the solid and liquid states from 76 to 900K. This is the first investigation of the thermal conductivity of InSb in the liquid state. Four samples cut from two polycrystalline ingots, with carrier density 7×10^{17} and 9×10^{17} cm^{-3}, were used for the measurements. The measurements were made with accuracy 1.5% by an absolute method under stationary thermal conditions, in an atmosphere of argon, as described elsewhere (Izv. AN AzSSR, no. 4, 3, 1946). The results show that the thermal conductivity of InSb in the solid state decreases in the entire investigated temperature interval, displaying no anomalous increase at high temperatures. The measured electric conductivity agreed with the results of others. The results indicate that at 770K the thermal conductivity due to pairs is only 14% of the total electronic conductivity and 20% of

Card 1/2

SHLYGIN, Ye. D.; MUKANOV, K. M.; GRISHIN, V. M.; MAGOMEDOV, S. G.

Supergene concentrations of gold in the gold ore deposits of northern Kazakhstan. Vest. AN Kazakh. SSR. 19 no.8:43-46 Ag '64. (MIRA 17:7)

SERGIYKO, Yu.A.; MAGOMEDOV, S.G.

Geology and localization of skarn-ore bodies in the Atansor deposit. Trudy Inst.geol.nauk AN Kazakh.SSR 6:58-67 '62.
(MIRA 16:6)
(Atansor Lake region--Ore deposits)

APPROVED FOR RELEASE: 06/23/11: CIA-RDP86-00513R001031400039-6

The Atansor Iron Ore Deposits in Kazakhstan

ASSOCIATION: Tsentral'no-Kazakhstanskoye geologicheskoye upravleniye
(The Central Kazakhstan Geology [illegible])

AVAILABLE: Library of Congress

Card 2/2 1. Magnetites 2. Magnetometers 3. Iron 4. Geology

MAGOMEDOV, S.G.

127-58-6-2/25

AUTHORS: Uzbekov, M.R. and Magomedov, S.G., Geologists

TITLE: The Atansor Iron Ore Deposits in Kazakhstan (Atansorskoye Zhelezorudnoye mestorozhdeniye v Kazakhstane)

PERIODICAL: Gornyy Zhurnal, 1958, Nr 6, pp 5-9 (USSR)

ABSTRACT: The Atansor ore deposits are situated on the south-western shore of Lake Atansor, in the Kokchetav Oblast' of Kazakhstan. The deposits were discovered in 1932, but were not fully explored until 1953, when magnetometric prospecting showed their importance. The ore bodies are formed by layers of magnetites, garnet-magnetites and amphbolic-magnetite scarns, the contents of iron reaching in some places 53.3%. Many other ore-deposits are known in this region, and many magnetic anomalies observed here permit the estimation of the available deposits of the Stepnyaksko-Atansor area to be 500-600 million tons. In future the Atansor region could serve as a second ore base for the Karagandinskiy metallurgicheskiy zavod (Karaganda Metallurgical Plant).

There is 1 map and 2 graphs.

Card 1/2

Name: MAGOMEDOV, Rasul Magomedovich

Dissertation: Social-Economic and political structure of Dagestan in the 18th and beginning of the 19th Centuries

Degree: Doc Historical Sci

Affiliation: Dagestan State Pedagogical Inst imeni Stal'skiy

Defense Date, Place: 10 Jan 57, Council of Azerbaydzhan State U imeni Kirov

Certification Date: 1 Jun 57

Source: BMVO 16/57

PA 66T1

MAGOMEDOV, R. M.

USSR/Academy of Sciences Jan 1948

"The Dagestan Scientific Research Base of the Academy of Sciences USSR," R. M. Magomedov, 3 pp

"Vest Ak Nauk SSSR" No 1

Organizational work of the Dagestan Base was completed in Jun 1946. Installation serves in the development of the Republic's economy, with particular emphasis on electric power, petroleum, gas, farming, and animal husbandry.

66T1

[redacted]

MAGOMEDOV, Nurali

Thoughtful boss. Neftianik 9 no.9:10 S '64 (MIRA 18:2)

1. Starshiy operator neftepromysla Gasha Dagestanskoy ASSR.

L 2214-66

ACCESSION NR: AP5019242

finding the invariant Laplacian, and solving the wave equation. The infinitesimal operators of U_3 are then determined as linear differential operators and their matrix elements are calculated in an arbitrary representation. The supermultiplets are classified in terms of rectangular diagrams in the (-S, 2T) plane. The infinitesimal operators are introduced as linear differential operators and their matrix elements are computed for an arbitrary representation. 'The authors thank V. B. Berestetskiy, I. Yu. Kobzarev, and L. B. Okun' for helpful discussions.' Orig. art. has: 35 formulas

ASSOCIATION: None

SUBMITTED: 03Feb65 ENCL: 00 SUB CODE: MA

NR REF SOV: 003 OTHER: 005

Card 2/2 DP

L 2214-66 EWT(d)/T IJP(c)
ACCESSION NR: AP5019242 UR/0056/65/049/001/0279/0291

AUTHORS: Magomedov, M. R.; Sudakov, V. V.

TITLE: Realization of the three-dimensional unitary group by 'spherical functions'

SOURCE: Zhurnal eksperimental'noy i teoreticheskoy fiziki, v. 49, no. 1, 1965, 279-291

TOPIC TAGS: group theory, matrix function, mathematic operator

ABSTRACT: The authors develop the mathematical formalism of the three-dimensional unitary group U_3 on the basis of a parametrization and realization of this group by means of special spherical functions which, for certain purposes, have definite advantages over the abstract-operator approach used by others. The method of realization is first illustrated by applying it to a three dimensional rotation group. In this case the method reduces to the parametrization of a manifold of unit vectors, determination of the invariant metric,

Card 1/2

L 1838-66
ACCESSION NR: AT5022280

Okun' for valuable comments." Orig. art. has: 5 figures and 35 formulas.

ASSOCIATION: [Magomedov] Fizicheskiy institut goskomiteta po ispol'zovaniy atomnoy energii SSSR, Yerevan (Physics Institute, State Committee on the Use of Atomic Energy); [Sudakov] Institut teoreticheskoy i eksperimental'noy fiziki goskomiteta po ispol'zovaniyu atomnoy energii SSSR (Institute of Theoretical and Experimental Physics, State Committee on the Use of Atomic Energy)

SUBMITTED: 28Dec64 ENCL: 00 SUB CODE: NP, MA

NO REF SOV: 003 OTHER: 005

Card 2/2

L 1838-66 EWT(d) IJP(c)
ACCESSION NR: AT5022280 UR/3138/64/000/311/0001/0031

31
29
B+1

AUTHOR: Magomedov, M. R.; Sudakov, V. V.

TITLE: Realization of a three-dimensional unitary group by "spherical functions" 76

SOURCE: USSR. Gosudarstvennyy komitet po ispol'zovaniyu atomnoy energii. Institut teoreticheskoy i eksperimental'noy fiziki. Doklady, no. 311, 1964. Realizatsiya trekhmernoy unitarnoy gruppy sfericheskimi fundtsiyami, 1-31

TOPIC TAGS: group theory, particle interaction, wave function

ABSTRACT: A convenient parametrization of the three-dimensional U_3 group is used to represent this group in the form of "spherical functions," which is preferable for certain purposes to the abstract-operator approach. The method consists of the following steps: (1) parametrization of the set of unit vectors, (2) determination of the invariant metric, (3) derivation of the invariant Laplacian, and (4) solution of the wave equation. The supermultiplets are classified in the form of square diagrams on the plane -S, 2T). Infinitesimal group operators are introduced in the form of linear differential operators, and their matrix elements are computed for an arbitrary representation. "In conclusion, the authors thank V. B. Berestetskiy, I. Yu. Kobzarev, and L. B.

Card 1/2

GARIBYAN, G.M.; MAGOMEDOV, M.R.

Radiation from an arbitrarily moving particle perpendicularly intersecting the interface of two media. Dokl. AN Arm. SSR 36 no.2:77-81 '64. (MIRA 17:3)

1. Fizicheskiy institut AN Armyanskoy SSR. Predstavleno akademikom AN Armyanskoy SSR A.N.Alikhanyanom.

S/252/63/036/002/001/003
D218/D308

Radiation emitted ...

cies. A general expression is obtained for the vector potential in both media as a function of time. These formulas become identical with the formulas for constant velocity only when the particle comes to rest at infinity. There is 1 figure.

ASSOCIATION: Fizicheskiy institut (Physics Institute)

PRESENTED: by A.N. Alikhanyan, Academician AS Arm.SSR

SUBMITTED: October 17, 1962

Card 2/2

APPROVED FOR RELEASE: 06/23/11: CIA-RDP86-00513R001031400039-6

S/252/63/036/002/001/003
D218/D308

AUTHORS: Garibyan, G.M. and Magomedov, M.R.

TITLE: Radiation emitted by an arbitrarily moving particle moving at right angles to the boundary of separation of two media

PERIODICAL: Akademiya nauk Armyanskoy SSR. Doklady, v. 36, no.2, 1963, 77-81

TEXT: Ginzburg and Frank (ZhETF, 16, 16, 1946) have shown that when a charged particle passes through the separation boundary between two media, a transition radiation is emitted. It is noted that in all previous calculations the velocity of the particle was assumed to be constant. The aim of the present work was to investigate the effect of irregular motion of the particle on the transition radiation. In a previous paper (ZhETF, 38, 18, 66, 1960) the first of the present authors studied this problem for an ultra-relativistic particle and high frequencies. The present theory is a generalization of these calculations to arbitrary velocity frequen-

Card 1/2

MAGOMEDOV, M. I., Cand Med Sci -- (diss) "Treatment of traumatic shock and blood loss with Caspian Sea water in experiment." Makhachkala, 1957. 20 pp (Ryazan' State Med Inst im Academician I. P. Pavlov), 350 copies (KL, 2-58, 116)

L 07836-67
ACC NR: AP6024673

strate surface. They also show that the growth kinetics can be explained by assuming the presence of two chemical reactions during the formation of the film, which have equal probability at higher temperatures (500 -- 3000). This explains, in particular, the disappearance of excess arsenic when zinc and cadmium are introduced in the gas phase, and the resultant absence of twinning. The results also show that introduction of impurities contributes to a balance in the stoichiometry and thereby decreases the number of growth defects. Numerous details concerning the influence of doping on the growth rate in different directions and concerning the internal structure of the layers are reported. The authors thank V. S. Imshtsau for an x-ray study of the crystals, O. S. Gordon for help with the experimental work, and Ye. I. Givargizov for critical remarks. Orig. art. has: 7 figures and 2 formulas.

SUB CODE: 20/ SUBM DATE: 28Jan66/ ORIG REF: 003/ OTH REF: 004

Card 2/2 bc

L 07836-67 EWT(m)/EWP(t)/ETI IJP(c) JD
ACC NR: AP6024673 (A) SOURCE CODE: UR/0070/66/011/004/0673/0680

AUTHOR: Magomedov, Kh. A.; Yarmukhamedov, Yu. N.; Sheftal', N. I.

ORG: Institute of Crystallography AN SSSR (Institut kristallografii AN SSSR)

TITLE: Influence of doping on the growth rate and morphology of epitaxial gallium arsenide films

SOURCE: Kristallografiya, v. 11, no. 4, 1966, 673-680

TOPIC TAGS: gallium arsenide, semiconducting film, epitaxial growing, semiconductor impurity, stoichiometry, twinning

ABSTRACT: The authors investigate the influence of Zn and Cd donors and Se and Te acceptors on the growth rate and structure of epitaxial films grown from the gas phase with the aid of a chemical reaction in an open system. The apparatus and the growth procedure were described earlier (in: Rost kristallov [Growth of Crystals] v. 6, Nauka, 1965, p. 388). The substrates used were gallium arsenide plates with various orientations and various types of conductivity. The results confirm earlier conclusions drawn by the authors (Kristall und Technik v. 1, no. 2, 1966) regarding the effect of stoichiometry of the components of the compound on the sub-

Card 1/2 UDC: 548.0:539.23

L 22865-66
ACC NR: AP6011360

at a given point. It is also established that in contrast to a corresponding two-dimensional scheme, the order of difference approximations is reduced to the first order in the purely three-dimensional case. Difference equations are derived, and the parameters of the desired point are obtained from two correlations along streamlines and two along bicharacteristics. Four elementary problems are considered: determination of points inside the flow, on the surface of the body, on a shock wave, and and on a free surface. The method described here is substantiated by numerical calculation of hypersonic flows past a spherically blunted cone with semiapex angles of 4°53' and 9°30' at $M_\infty = 6$ and at an angle of attack $\alpha = 5°$. The author thanks V. V. Lunev for constant interest in the work. Orig. art. has: 3 figures and 35 formulas. [AB]

SUB CODE: 20/ SUBM DATE: 13Mar65/ ORIG REF: 006/ OTH REF: 007/ ATD PRESS: 4232

Card 2/2 LC

L 22865-66 EWT(1)/EWP(m)/EWA(d)/EWA(1) RM/WW

ACC NR: AP6011360 SOURCE CODE: UR/0208/66/006/002/0313/0325

AUTHOR: Magomedov, K. M. (Moscow)

ORG: none

TITLE: A method of characteristics for numerical calculation of three-dimensional flows

SOURCE: Zhurnal vychislitel'noy matematiki i matematicheskoy fiziki, v. 6, no. 2, 1966, 313-325

TOPIC TAGS: supersonic aerodynamics, supersonic flow, three dimensional flow, steady flow, shock wave, flow analysis

ABSTRACT: A number (of methods of characteristics for numerical calculation of three-dimensional supersonic flows or unsteady two-dimensional problems of gas dynamics are evaluated and their complexity stressed. A new approach is outlined by which relative simplicity and uniformity are attained. The equations of a steady three-dimensional supersonic flow are transformed to an equivalent characteristic form which is not the only possible one. Therefore, a general form of characteristic correlations (compatibility conditions) is considered along a single-parameter family of bicharacteristics passing through a given point. It is demonstrated that an equation describing supersonic steady flow can be reduced by equivalent transformations to a system containing variables only along streamlines and bicharacteristic directions

Card 1/2 UDC: 517.9:533.7

L 12773-66

ACC NR: AP6003369

son of experimental weight loss measurement data with calculated data served as a criterion of equilibrium. It was shown that the near equilibrium conditions for GaAs thin film deposition were: 1000C at the GaAs source, 640C at the substrate, 2.26×10^{-3} molar iodine concentration in the $H_2 + I_2$ mixture, and 5cm/sec space velocity over the source. Supersaturation in the deposition region increased from 2 to 7 when temperature was decreased from 850 to 600C. Enthalpy ΔH was also calculated from the experimental data both for the reaction at the source: $2GaAs_{(s)} + I_{2(g)} = 2GaI_{(g)} + 1/2\ As_{4(g)}$ and for the above given reaction in the deposition region. The ΔH_{1100K} of the first reaction was found lower than the value calculated from literature data, and ΔH_{1000K} of the second reaction was nearly the same as the value based on literature data. Orig. art. has: 5 figures, 1 table, and 22 formulas. [JK]

SUB CODE: 07, 20/ SUBM DATE: 03May65/ ORIG REF: 002/ OTH REF: 006/ ATD PRESS: 4184

Card 2/2 HW

L 12773-66 EWI(m)/EWP(t)/EWP(b) IJP(c) JD/JW/JG

ACC NR: AP6003369 SOURCE CODE: UR/0363/66/002/001/0117/0123

AUTHOR: Magomedov, Kh. A.

ORG: Institute of Crystallography, Academy of Sciences SSSR (Institut kristallografii Akademii Nauk SSSR)

TITLE: Equilibrium conditions and supersaturation in the GaAs-I_2-H_2 system

SOURCE: AN SSSR. Izvestiya. Neorganicheskiye materialy, v. 2, no. 1, 1966, 117-123

TOPIC TAGS: crystal growth, epitaxial growing, gallium arsenide, thin film, chemical transport reaction, reaction mechanism

ABSTRACT: Supersaturation of the vapor phase in the GaAs deposition region has been calculated as a function of crystallization temperature in the 600—850 C range in the open flow system of gallium-arsenide-iodine-hydrogen. This research work was prompted by the lack of data on supersaturation which is a very important parameter of crystallization, and determination of which helps to understand the mechanism of crystal growth by chemical transport reactions. The known formula for isobaric-isothermic potential was used for calculating supersaturation on the basis of the experimental equilibrium data which were obtained for the reaction: $2GaAs_{(s)} + GaI_3(g) \rightleftarrows 3GaI(g) + 1/2\ As_4(g)$ in the deposition region of the open flow system. The open flow apparatus was a vertical tube in which hydrogen saturated with iodine vapors was flowing at atmospheric pressure and in a temperature gradient through a layer of GaAs. Compari-

Card 1/2 UDC: 541.123.3-546.681'191-546.15-546.11

M. GOMELOV, Kh. ..., YASHUKHANOV, Yu.N.

Effects of growth of epitaxial films of gallium arsenide.
Izv. AN SSSR. Neorg. mat. 1 no.12:2120-2127 D '65.
(MIRA 18:12)

1. Institut kristallografii AN SSSR. Submitted May 31, 1965.

L 15205-66
ACC NR: AP6001227

flow rate is 5 cm/sec, no growth figures whatever form on surface A (111) if the surface of the substrate is subjected to annealing and gas etching prior to the growing. Authors thank Yu. N. Yarmukhamedov for assistance in the microscopic study and in obtaining photomicrographs of the film. Orig. art. has: 5 figures and 1 formula.

SUB CODE: 11, 20 / SUBM DATE: 31May65 / ORIG REF: 002 / OTH REF: 016

Card 2/2

APPROVED FOR RELEASE: 06/23/11: CIA-RDP86-00513R001031400039-6

L 15205-66 EWT(m)/T/EWP(t)/EWP(b) LJP(c) JD/JG

ACC NR: AP6001227 (A) SOURCE CODE: UR/0363/65/001/012/2113/2119

AUTHOR: Magomedov, Kh. A.; Sheftal', N. N.

ORG: Institute of Crystallography, Academy of Sciences SSSR (Institut kristallografii Akademii nauk SSSR)

TITLE: Mechanism of growth and defects of epitaxial gallium arsenide films

SOURCE: AN SSSR. Izvestiya. Neorganicheskiye materialy, v. 1, no. 12, 1965, 2113-2119

TOPIC TAGS: epitaxial growing, gallium arsenide, crystal defect

ABSTRACT: The effect of mainly two factors, the crystallization temperature in the 550 — 850C temperature range and partial pressure of iodine in the 0.6 — 8 mm Hg pressure range, on the perfection of GaAs epitaxial films was investigated. At 640 — 650C packing defects in the form of equilateral triangles, isosceles trapezoids, and single lines are formed on surface A (111). Sometimes growth pits also appear. At higher temperatures of the deposition zone (700 — 850C), only growth pits in the form of trigonal, ditrigonal, hexagonal truncated, and complete pyramids are formed. The formation of stacking faults and growth pits is due to the presence of oxide islets of β-Ga_2O_3 on the substrates. No growth pits or stacking faults are formed on surface B (111), but penetration twins appear at low temperatures (640C) and truncated and complete pyramids are formed at 700 — 750C. When the GaAs source is at 1000C and the substrates at 640C, the iodine partial pressure is 2.26×10^{-3} mm Hg and the

Card 1/2 UDC: 546.681'191

The constructed device makes it possible to reproduce the experimental conditions more accurately, to carry out the process under conditions close to equilibrium, and to produce and maintain in the working volume the required temperature profile and other parameters of the process. The device was used to prepare single-crystal epitaxial gallium arsenide films grown on single-crystal gallium arsenide and germanium substrates. It is also suitable for preparing epitaxial films of silicon, germanium, and other semiconducting materials. Authors thank V.F. Martynov for his high-quality glass-blowing work. Orig. art. has: 1 figure.

SUB CODE: 20, 07 / SUBM DATE: none / ORIG REF: 001 / OTH REF: 003

bvk

L 15968-66 EWT(m)/T/EWP(t)/EWP(b) IJP(c) JD/JG

ACC NR: AT6002273 (A) SOURCE CODE: UR/2564/65/006/000/0388/0392

AUTHOR: Magomedov, Kh. A.; Sheftal', N.N.

ORG: none

TITLE: Growing of epitaxial gallium arsenide films. (Paper presented at the Third Conference on Crystal Growing held in Moscow from 18 to 25 November, 1963.)

SOURCE: AN SSSR. Institut kristallografii. Rost kristallov, v. 6, 1965, 388-392

TOPIC TAGS: epitaxial growing, gallium arsenide

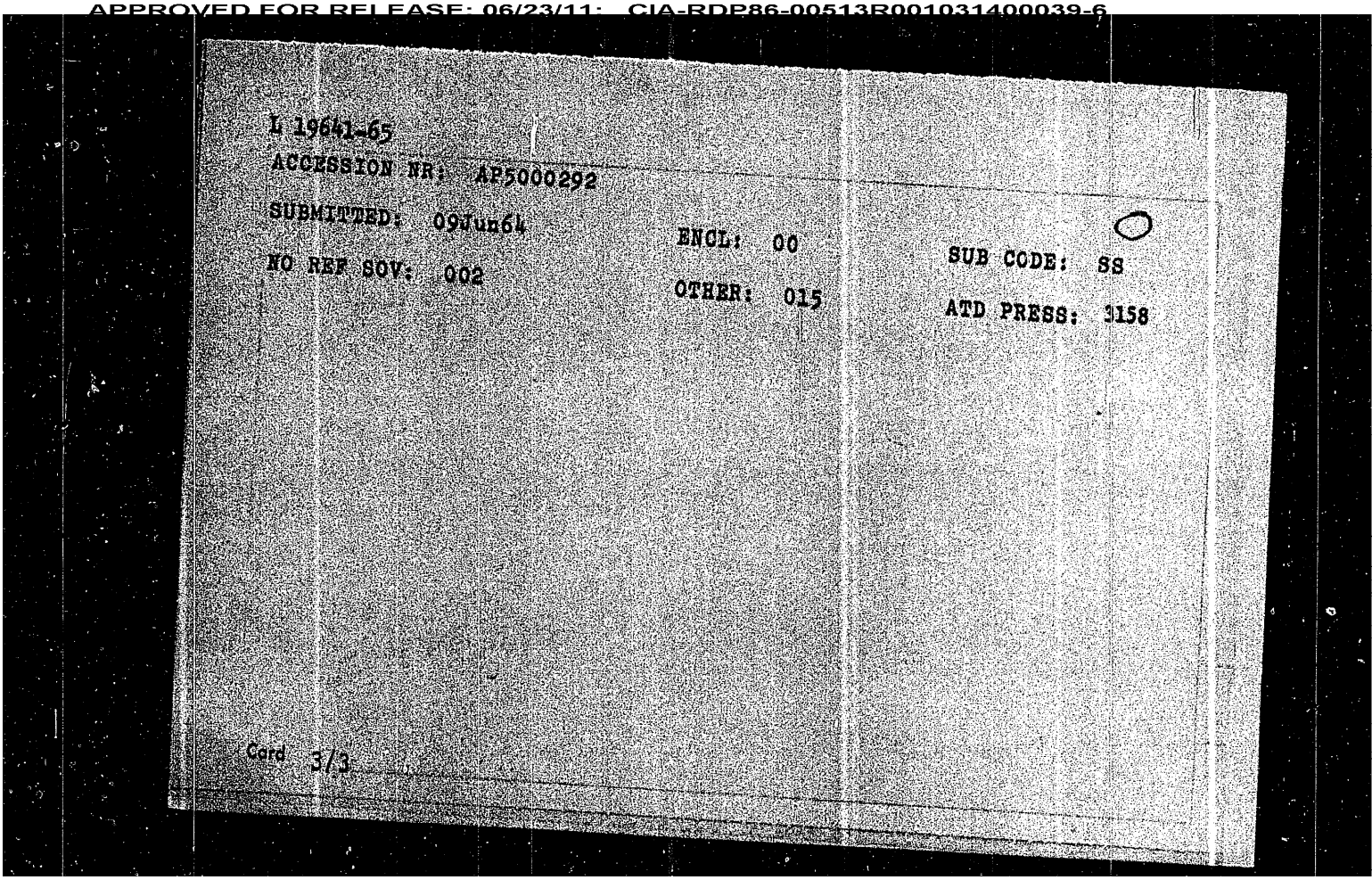
ABSTRACT: The article describes the apparatus and method developed for preparing epitaxial gallium arsenide films by the open hydrogen-iodide method. In this method, a stream of hydrogen carries iodine vapor, which encounters gallium arsenide in the high-temperature zone and reacts as follows:

$$2GaAs + J_2 = 2GaJ + \frac{1}{2}As_4.$$

The reaction products are carried to a cooler zone, where the second reaction occurs on the surface of a substrate:

$$2GaAs + GaJ_3 \rightleftarrows 3GaJ + As_4.$$

Card 1/2



L 19641-65
ACCESSION NR: AP5000292
SUBMITTED: 09Jun64
ENCL: 00
SUB CODE: SS
NO REF SOV: 002
OTHER: 015
ATD PRESS: 3158

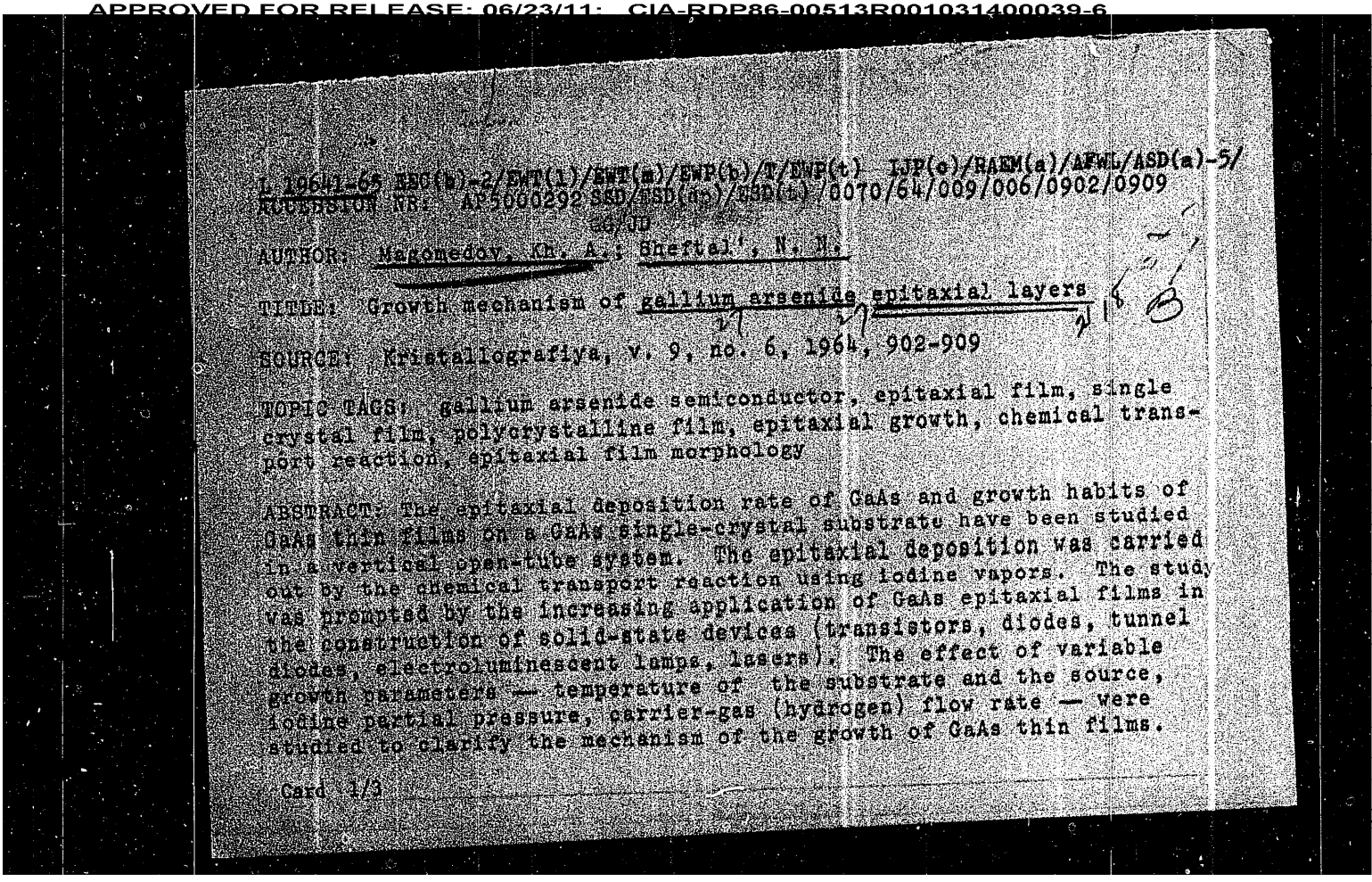
Card 3/3

L 19641-65
ACCESSION NR: AP5000292

Experiments were carried out in a three-zone furnace with individual temperature control in each zone. The source (in zone 2) was n-type GaAs single crystals. The substrate (in zone 3) was chemically etched, weighed, and gas etched in an iodine vapor stream. The epitaxial films had the same conductivity type and resistivity as the source. Microinterferometric, micrographic, and electronographic investigations indicated that the deposition rate and morphology of epitaxial films on (111) A and (1$\bar{1}\bar{1}$) B planes depend mainly on substrate temperature (in the 550—700C range), iodine partial pressure (in the 0.7—6.2 mm Hg range), and hydrogen flow rate near the source (in the 5—30 cm/sec range). Optimum conditions were established for a single-crystal deposit on the (111) plane, without geometrical surface patterns. Polycrystalline layers were observed on both planes of the substrate at certain temperatures and at iodine partial pressure. Various geometrical patterns including twins were always present on (1$\bar{1}\bar{1}$) B surfaces. The maximum deposition rate was 90 μ/hr — on the (111) A plane. Orig. art. has: 8 figures and 2 formulas.

ASSOCIATION: Institut kristallografii AN SSSR (Institute of Crystallography, AN SSSR)

Card 2/3



L 19641-65 EEC(b)-2/EWT(l)/EWT(m)/EWP(b)/T/EWP(t) IJP(c)/RAEM(a)/AFWL/ASD(a)-5/
ACCESSION NR: AP5000292 SSD/ASD(ap)/ESD(t) 0070/64/009/006/0902/0909
ES/JD

AUTHOR: Magomedov, Kh. A.; Sheftal', N. N.

TITLE: Growth mechanism of gallium arsenide epitaxial layers

SOURCE: Kristallografiya, v. 9, no. 6, 1964, 902-909

TOPIC TAGS: gallium arsenide semiconductor, epitaxial film, single crystal film, polycrystalline film, epitaxial growth, chemical transport reaction, epitaxial film morphology

ABSTRACT: The epitaxial deposition rate of GaAs and growth habits of GaAs thin films on a GaAs single-crystal substrate have been studied in a vertical open-tube system. The epitaxial deposition was carried out by the chemical transport reaction using iodine vapors. The study was prompted by the increasing application of GaAs epitaxial films in the construction of solid-state devices (transistors, diodes, tunnel diodes, electroluminescent lamps, lasers). The effect of variable growth parameters — temperature of the substrate and the source, iodine partial pressure, carrier-gas (hydrogen) flow rate — were studied to clarify the mechanism of the growth of GaAs thin films.

Card 1/3

ACC NR: AP7002930

is a local Cartesian system; $F_i = F_i(\beta, \gamma, r)$, $Q = Q(P, S)$, $Q_i = Q_i(P, S)$, $k_i \nabla f$ is the derivative in the direction of the vector k_i. The remainder of the article is devoted to a mathematical solution of the problem on the above premises. The paper was presented by Academician Dorodnitsyn, A. A. on 6 March 1966. Orig. art. has: 13 formulas and 2 figures.

SUB CODE: 20/ SUBM DATE: 28Feb66/ ORIG REF: 007/ OTH REF: 001

Card 2/2

ACC NR: AP7002930 SOURCE CODE: UR/0020/66/171/006/1297/1300

AUTHOR: Magomedov, K. M.

ORG: Moscow Physicotechnical Institute (Moskovskiy fiziko-tekhnicheskiy institut)

TITLE: Calculation of surfaces by space method characteristics

SOURCE: AN SSSR. Doklady, v. 171, no. 6, 1966, 1297-1300

TOPIC TAGS: gas dynamics, aerodynamic characteristic, aerodynamic boundary layer, mathematic analysis

ABSTRACT: The article demonstrates mathematically that in different schemes for finding the points of the required boundary surfaces (shock wave, free surface), it is necessary and sufficient to make use of a single combination of the differential equations of gas dynamics. It assumes the equations for the steady-state supersonic movement of an ideal gas in the form:

$$\cos\gamma k_2\nabla\beta + k_3\nabla\gamma + Q_1 k_1\nabla p = F_1, \quad \cos\gamma k_1\nabla\beta + Qk_2\nabla p = F_2,$$
$$k_1\nabla\gamma + Qk_3\nabla p = F_3, \quad k_1\nabla S = 0, \qquad (1)$$

where the velocity vector in cylindrical coordinates z, r, φ is taken in accordance with the relationship $\mathbf{V} = V\{\cos\beta\cos\gamma,\ \sin\beta\cos\gamma,\ \sin\gamma\}$; $k_1 = \mathbf{V}/V$, $k_2 = \cos^{-1}\gamma\,\partial k_1/\partial\beta$, $k_3 = \partial k_1/\partial\gamma$

UDC: 533.6.011.3/5

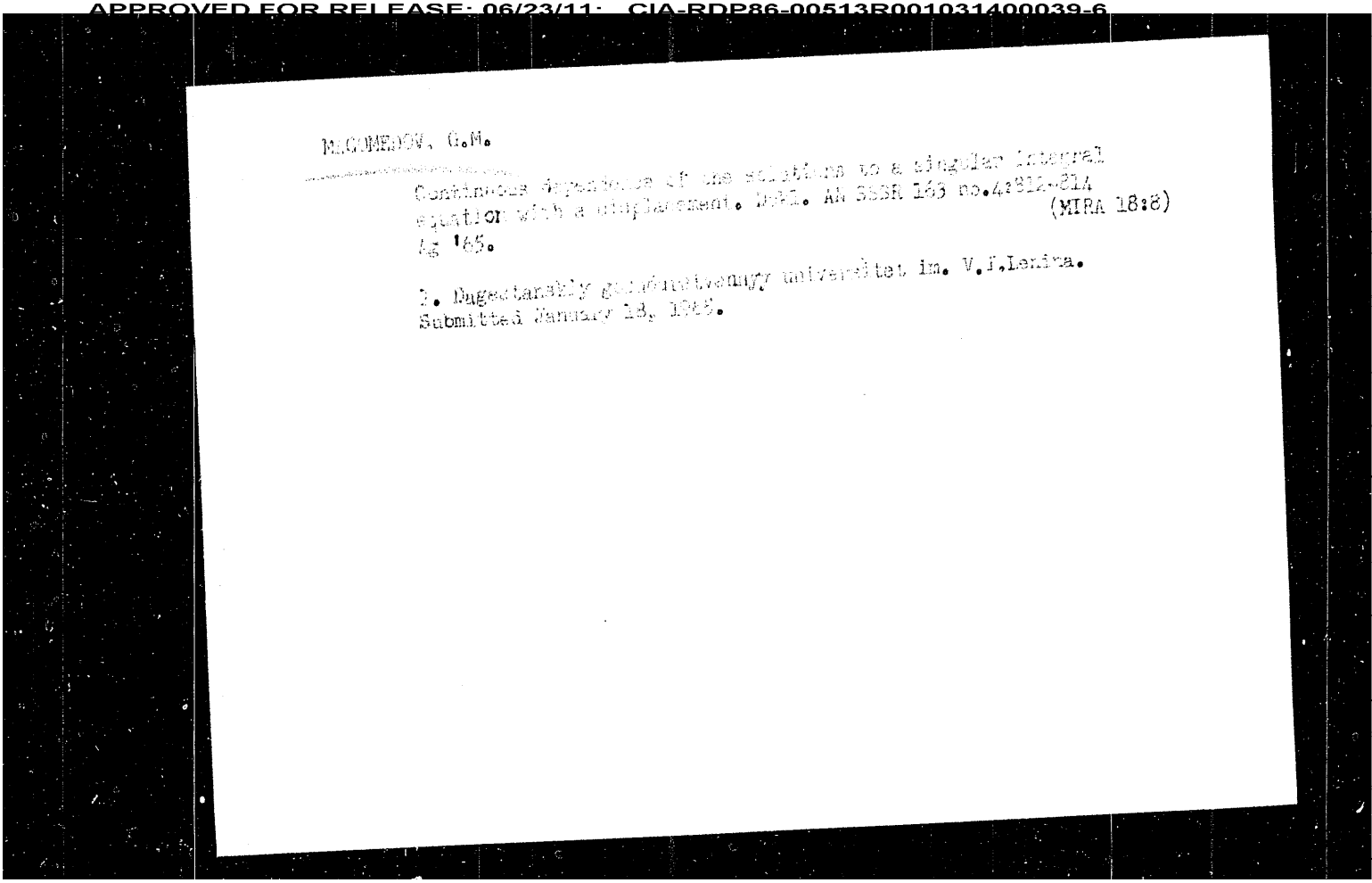
Card 1/2

MAGOMEDOV, K.M.

Supersonic flow about blunt bodies with a known sonic point. Izv. AN SSSR.Otd.tekh.nauk.Mekh.i mashinostr. no.1:111-117 Ja-F '63. (MIRA 16:2)

(Aerodynamics, Supersonic)

APPROVED FOR RELEASE: 06/23/11: CIA-RDP86-00513R001031400039-6



MAKAROV, G.M.

Continuous dependence of the solutions of a singular integral equation with a displacement. Izv. AN SSSR 160 no.4:811-814 (MIRA 18:8)
Ag '65.

1. Dagestanskiy gosudarstvennyy universitet im. V.I.Lenina.
Submitted January 18, 1965.

L 10644-66

ACC NR: AP6002075

drops in the sequence $-OC_2H_5 > -OC_3H_{7\text{-}n.} > -OCH_2-CH=CH_2 > -OCH_3 > -OC_4H_9$. 2[2-(Ethoxy)-5-hexen-3-ynyl]cyclopentadienyltricarbonylmanganese improves the octane rating by two numbers as compared with CTM. 4) Introduction of acyl or benzayl groups into the CTM molecule lowers its antiknock effectiveness. Orig. art. has: 1 fig. and 6 tables. [BO]

SUB CODE: 21/ SUBM DATE: 12Nov64/ ORIG REF: 003/ OTH REF: 002/ ATD PRESS: 4169

Card 2/2

L 10644-66 EWT(m)/T WE/RM

ACC NR: AP6002075 SOURCE CODE: UR/0204/65/005/006/0892/0896

AUTHOR: Nesmeyanov, A. N.; Zaytsev, V. A.; Anisimov, K. N.; Lerner, M. O.; Kolobova, N. Ye.; Poretskaya, A. P.; Magomedov, G. K.

ORG: Institute of Heterorganic Compounds AN SSSR (Institut elementoorganicheskikh soyedineniy AN SSSR)

TITLE: Antiknock effectiveness of certain organomanganese compounds

SOURCE: Neftekhimiya, v. 5, no. 6, 1965, 892-896

TOPIC TAGS: antiknock compound, organomanganese compound, fuel additive

ABSTRACT: The antiknock effectiveness of manganese carbonyl (MC) and of cyclopentadienyltricarbonylmanganese (CTM) derivatives was compared with that of CTM and tetraethyllead (TEL). The effectiveness of the individual organomanganese compounds in different concentrations was studied in various fuels by the standard motor method for determining the octane number. It was shown that for a given metal content in the fuel: 1) the antiknock effectiveness of MC in comparison with that of CTM and TEL is as follows: a) In automotive gasolines A-66 and A-72, lower; b) in a mixture of isooctane (60%) and heptane (40%), nearly the same; c) in the aviation gasoline B-95/130, lower. 2) The antiknock effectiveness of MC-CTM mixture in B-95/130 gasoline is equal to that of CTM. 3) The antiknock effectiveness of 2[2-(alkoxy)-5-hexen-3-ynyl]cyclopentadienyltricarbonylmanganeses depends on the alkoxy group and

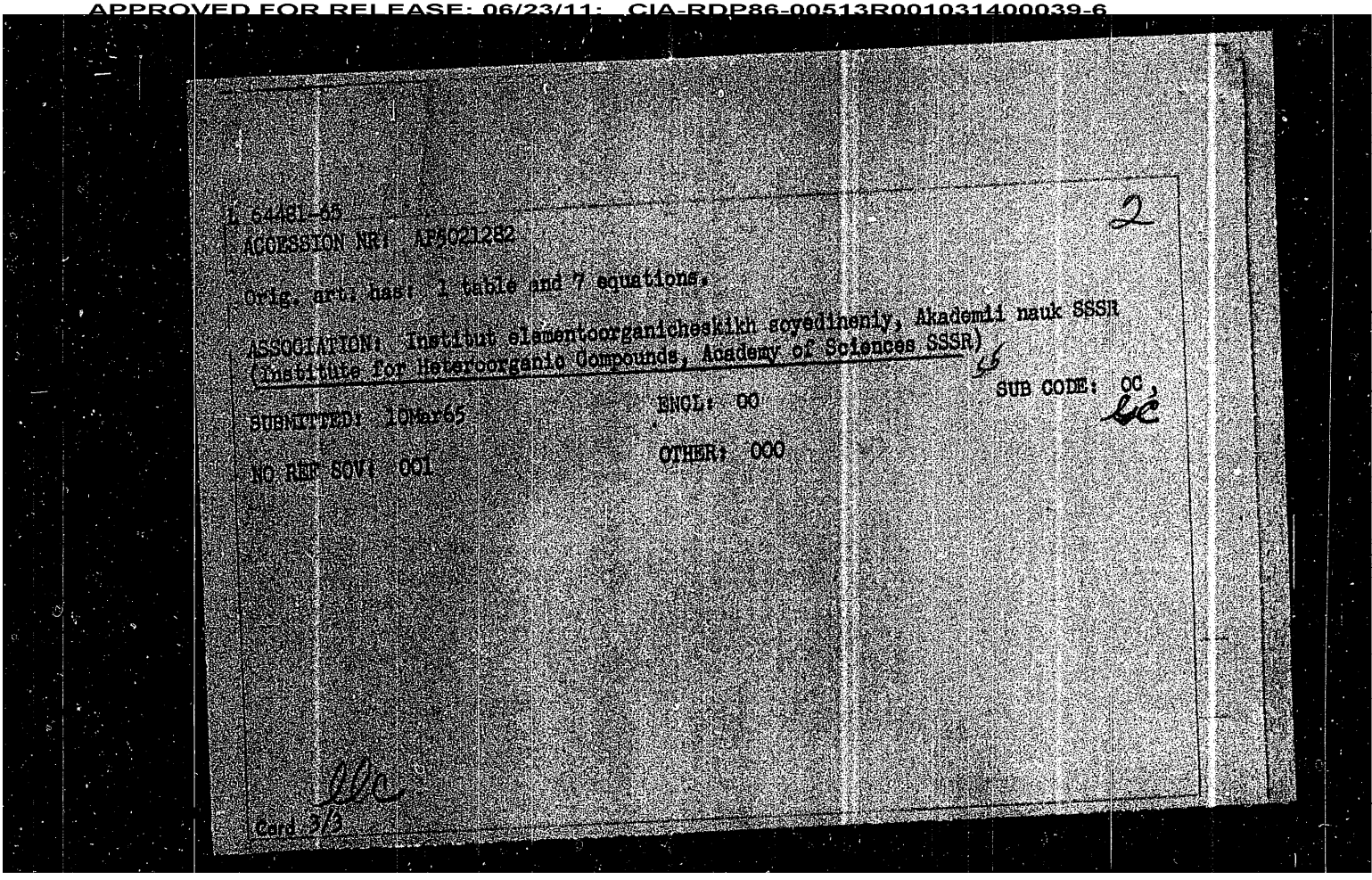
UDC: 547.514.72'171.1:665.521.23

Card 1/2

ANISIMOV, K.N.; KOLOBOVA, N.Ye.; MAGOMEDOV, G.K.-I.

Synthesis and isomerization of
4-hydroxy-4-methyl-2-heptenyne-6-yl-2-cyclopentadienyl-
manganesetricarbonyl. Dokl. AN SSSR 165 no.4:877-880 D '65.
(MIRA 19:1)

1. Institut elementoorganicheskikh soyedineniy AN SSSR.
Submitted April 26, 1965.



L 64481-65
ACCESSION NR: AP5021282

2

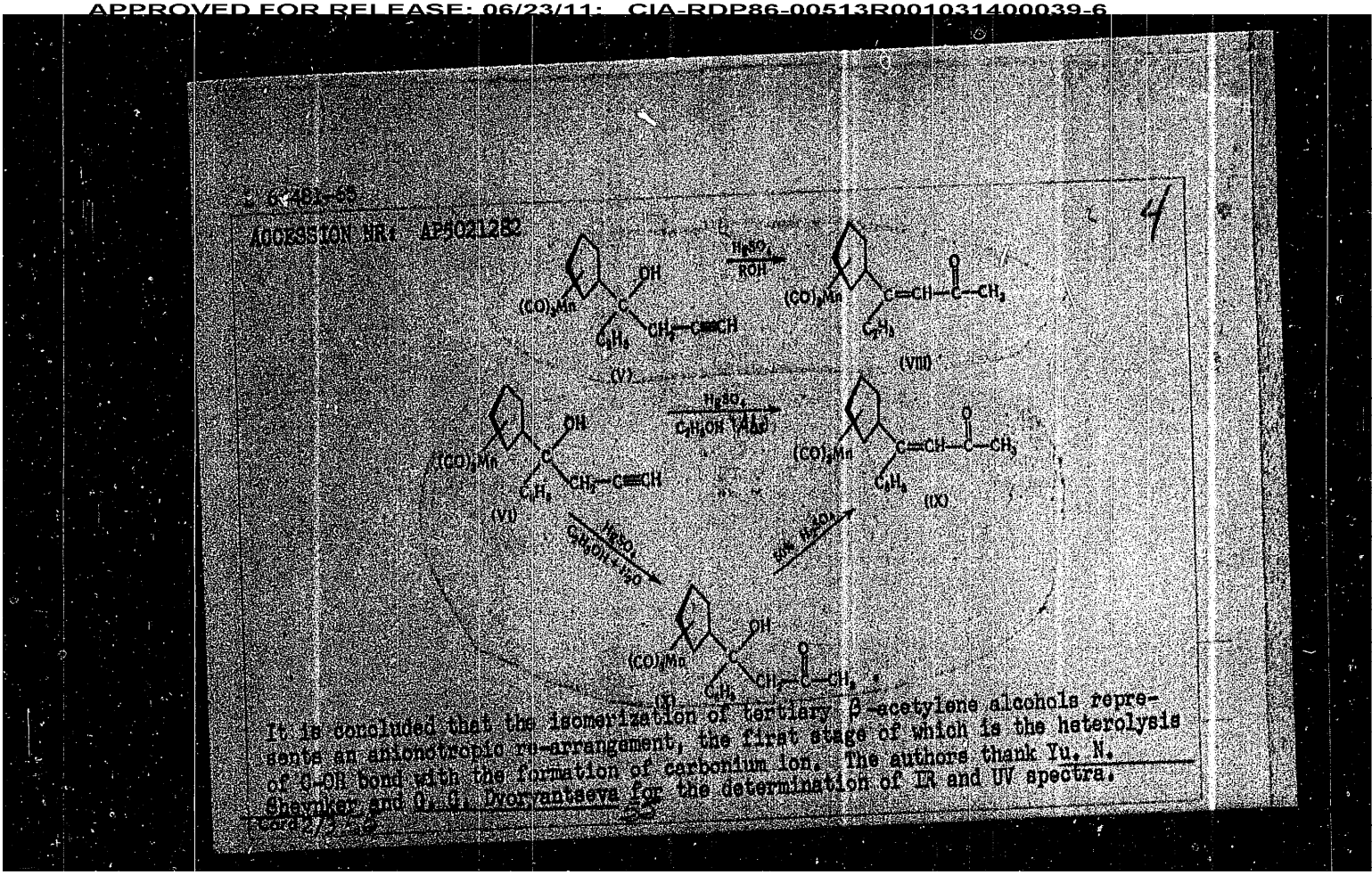
Orig. art. has: 1 table and 7 equations.

ASSOCIATION: Institut elementoorganicheskikh soyedineniy, Akademii nauk SSSR (Institute for Heteroorganic Compounds, Academy of Sciences SSSR)

SUBMITTED: 10Mar65 ENCL: 00 SUB CODE: OC, GC

NO REF SOV: 001 OTHER: 000

Card 2/3



L 62461-65
ACCESSION NR: AP5021282

4

It is concluded that the isomerization of tertiary β-acetylene alcohols represents an anionotropic πσ-arrangement, the first stage of which is the heterolysis of β-OH bond with the formation of carbonium ion. The authors thank Yu. N. Chayrikov and O. G. Dvorantseva for the determination of IR and UV spectra.

Card 2/3 23